## What is claimed is:

	1. A method for improvement of edge breakdown
	caused by edge electrical field at a tunnel oxide of a high-density
5	flash memory by a shielded bird's beak, the method comprising
	the steps of:
	forming a plurality of trenches on a substrate for
	isolating a plurality of active regions;
	forming a liner oxide on the plurality of trenches and
10	extending to respective edges of the plurality of
	active regions;
	depositing a first oxide filled in the plurality of
	trenches for forming a plurality of shallow trench
	isolations;
15	depositing a second oxide for covering the plurality of
	shallow trench isolations and active regions;
	etching the second oxide for forming a plurality of
	bird's beak spacers at the respective edges of the
	plurality of active regions; and
20	forming a tunnel oxide layer on the plurality of active

2. The method according to claim 1, wherein the step of forming a plurality of trenches comprises the steps of: forming a pad nitride on the substrate;

regions.

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defining a pattern for the plurality of shallow trench isolations on the pad nitride; and etching the substrate with the pad nitride as a mask for forming the plurality of trenches.

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3. The method according to claim 1, wherein the step of forming a plurality of shallow trench isolations comprises the steps of:

depositing the first oxide by a high-density plasma deposition; and

chemical-mechanical polishing the first oxide.

- 4. The method according to claim 1, wherein the step of forming a second oxide comprises a high-temperature oxide deposition.
- 5. The method according to claim 1, further comprising the steps of:

forming a sacrificial oxide on the plurality of the active regions after the formation of a plurality of bird's beak spacers; and

removing the sacrificial oxide.

6. The method according to claim 1, wherein the liner oxide forms a plurality of initial bird's beaks at the

respective edges of the plurality of active regions.

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- 7. The method according to claim 6, wherein the bird's beak spacers are self-aligned to and shield the plurality of initial bird's beaks.
- 8. A method for improvement of edge breakdown caused by edge electrical field at a tunnel oxide of a high-density flash memory by a shielded bird's beak, the method comprising the steps of:

depositing a pad nitride on a substrate;

- defining a pattern for an active region and a shallow trench isolation on the pad nitride;
- etching the substrate with the pad nitride as a mask for forming a trench;
- forming a liner oxide on the trench and extending to an edge of the active region for intruding under the pad nitride to form a bird's beak;
- depositing a first oxide filled in the trench and covering on the pad nitride;

polishing-back the first oxide;

removing the pad nitride;

- depositing a second oxide for covering the first oxide and active region;
- etching the second oxide for forming a bird's beak

spacer at an edge of the active region; and forming a tunnel oxide layer on the active region.

9. The method according to claim 8, wherein the step of forming a liner oxide comprises a high-temperature oxidation at a temperature of about 1100-1200 ℃.

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- 10. The method according to claim 8, wherein the step of depositing a first oxide comprises a high-density plasma deposition at a temperature of about 400-550 ℃.
  - 11. The method according to claim 8, wherein the step of polishing-back the first oxide comprises chemical-mechanical polishing with the pad nitride as a etch-stop layer.
  - 12. The method according to claim 8, wherein the step of depositing a second oxide comprises a high-temperature oxide deposition at a temperature of about 800-900  $^{\circ}$ C.
- 13. The method according to claim 12, wherein the first and second oxides are fused with each other.
- 14. The method according to claim 8, wherein the step of etching the second oxide comprises an over-etching of a

thickness of the substrate at the active region.

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15. The method according to claim 8, further comprising the steps of:

forming a sacrificial oxide on the active region after the formation of the bird's beak spacer; and removing the sacrificial oxide.